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# TRANSISTORS, POWER, NPN, BASED ON TYPE 2N5926 ESCC Detail Specification No. 5208/005

# ISSUE 1 October 2002





#### **ESCC Detail Specification**

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# TRANSISTORS, NPN POWER TRANSISTOR BASED ON TYPE 2N5926

ESA/SCC Detail Specification No. 5208/005



# space components coordination group

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Issue/Rev.	Date	SCCG Chairman	ESA Director General or his Deputy
Issue 1	May 1980	-	1 -0 /
Revision 'A'	February 1992	Tomoment	Llub
Revision 'B'	August 1996	Sa_mit	Horm



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#### **DOCUMENTATION CHANGE NOTICE**

T T					
Rev. Letter	Rev. Date	CHANGE Reference Item	Approved DCR No.		
'A'	Feb. '92	This Issue incorporates all modifications agreed on the basis of Policy DCR 21016 for adaptation to new qualification requirements.  P1. Cover page P2. DCN P4. Table of Contents: "Appendices" title added P5. Para. 1.2: Paragraph amended P6. Table 1(a): "Lead Material and/or Finish" column amended P11. Para. 2: MIL-STD-1276 deleted, "ESA/SCC Basic Spec. No. 23500" added Para. 4.1: Additional text added Para. 4.2.2: PIND deviation deleted P13. Para. 4.4.2: Paragraph amended P18. Table 3(a), (b): Reference to Note 2 deleted, Note 1 put under this table	None None 21019 21021 21025 21025 21019 21043 21025 21047		
		This document has been transferred from hardcopy to electronic format. The content is unchanged but minor differences in presentation exist.			
'B'	Aug. '96	P1. Cover page P2. DCN P5. Para. 1.7 : Text amended	None None 21083		



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APPENDICES (Applicable to specific Manufacturers only)

None.



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#### 1. **GENERAL**

#### 1.1 SCOPE

This specification details the ratings, physical and electrical characteristics, test and inspection data for a Transistor, Power, NPN, based on Type 2N5926.

It shall be read in conjunction with ESA/SCC Generic Specification No. 5000, the requirements of which are supplemented herein.

#### 1.2 COMPONENT TYPE VARIANTS

See Table 1(a).

#### 1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the transistors specified herein are scheduled in Table 1(b).

#### 1.4 PARAMETER DERATING INFORMATION

The derating information applicable to the transistors specified herein is shown in Figure 1.

#### 1.5 PHYSICAL DIMENSIONS

The physical dimensions of the transistors specified herein are shown in Figure 2.

#### 1.6 FUNCTIONAL DIAGRAM

The functional diagram showing lead identification, of the transistors specified herein, is shown in Figure 3.

#### 1.7 <u>HIGH TEMPERATURE TEST PRECAUTIONS</u>

For tin-lead plated or solder-dipped lead finish, all tests to be performed at a temperature that exceeds +125°C shall be carried out in a 100% inert atmosphere.



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# TABLE 1(a) - TYPE VARIANTS

VARIANT	CASE	FIGURE	LEAD MATERIAL AND FINISH
01	TO63	2	D2
02	TO63	2	D3 or D4



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#### **TABLE 1(b) - MAXIMUM RATINGS**

No.	CHARACTERISTICS	SYMBOL	MAXIMUM RATINGS	UNIT	REMARKS
1	Collector-Emitter Voltage	$V_{CE}$	120	Vdc	
2	Collector-Base Voltage	V <sub>CB</sub>	150	Vdc	
3	Emitter-Base Voltage	V <sub>EB</sub>	10	Vdc	
4	Emitter Current (Continuous)	ΙΕ	50	Adc	
5	Base Current (Continuous)	lΒ	10	Adc	
6	Power Dissipation (Continuous)	P <sub>tot</sub>	350	W	T <sub>case</sub> ≤ +25°C Note 1
7	Operating Junction Temperature Range	T <sub>op</sub>	-65 to +200	°C	
8	Storage Temperature Range	T <sub>stg</sub>	-65 to +200	°C	
9	Soldering Temperature	T <sub>sol</sub>	+ 260	°C	Note 2

#### **NOTES**

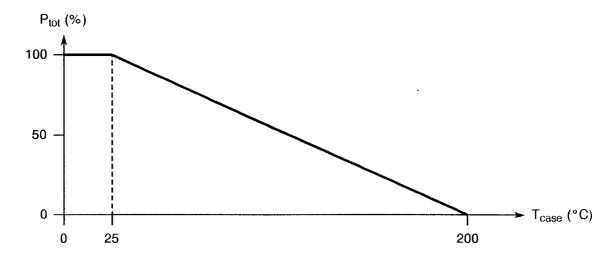
- 1. For  $T_{case}$  > +25°C, derate at 2.15°C/W.
- 2. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.



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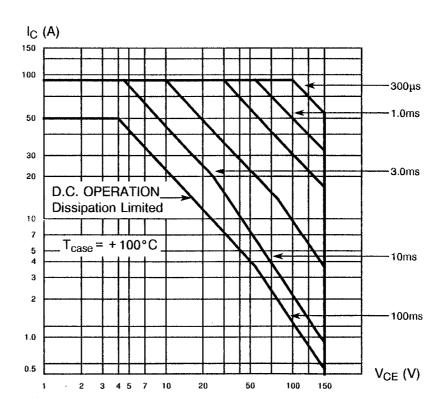
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#### FIGURE 1(a) - PARAMETER DERATING INFORMATION



Power Dissipation versus Temperature

#### FIGURE 1(b) - SAFE OPERATING AREA (CONTINUOUS D.C.)

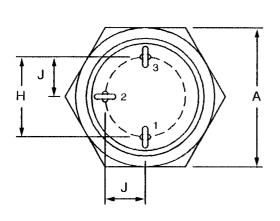


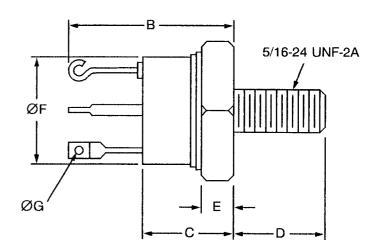


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#### **FIGURE 2 - PHYSICAL DIMENSIONS**





- 1. Emitter.
- 2. Base.
- 3. Collector.

SYMBOL	MILLIM	MILLIMETRES		
STIVIDOL	MIN.	MAX.	NOTES	
Α	21.72	22.23		
В	24.76	26.16	,	
С	12.70	13.59		
D	11.68	12.57		
Е	3.17	3.43		
ØF	19.05	19.43		
ØG	1.52	2.66		
Н	12.40	12.90		
J	6.22	6.49		

#### **NOTES**

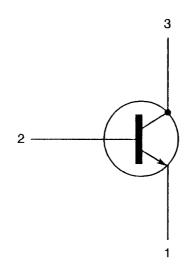
- 1. Index area: the leads shall be orientated as shown when viewed from above.
- 2. The collector shall be electrically connected to the case.



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# FIGURE 3 - FUNCTIONAL DIAGRAM AND SCHEMATIC SYMBOL



- 1. Emitter.
- 2. Base.
- 3. Collector.



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#### 2. APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:-

- (a) ESA/SCC Generic Specification No. 5000 for Discrete Semiconductor Components.
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices.
- (c) ESA/SCC Basic Specification No. 23500, Requirements for Lead Materials and Finishes for Components for Space Application.
- (d) MIL-STD-105, Sampling Procedure and Tables for Inspection by Attributes.

#### 3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply.

#### 4. REQUIREMENTS

#### 4.1 GENERAL

The complete requirements for procurement of the transistors specified herein are stated in this specification and ESA/SCC Generic Specification No. 5000. Deviations from the Generic Specification, applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

#### 4.2 <u>DEVIATIONS FROM GENERIC SPECIFICATION</u>

#### 4.2.1 Deviations from Special In-process Controls

None.

#### 4.2.2 <u>Deviations from Final Production Tests (Chart II)</u>

- (a) Para. 9.1, "Internal (Pre-encapsulation) Visual Inspection": Shall be performed in accordance with the Power Tech. Precap Visual document, dated 1st February 1974.
- (b) Para. 9.2.1, "Bond Strength Test": Shall not be performed.
- (c) Para. 9.6, "Constant Acceleration": Change Acceleration Level to 5000g.



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#### 4.2.3 <u>Deviations from Burn-in and Electrical Measurements (Chart III)</u>

(a) Para. 7.1.1(a), High Temperature Reverse Bias test: Not applicable.

#### 4.2.4 <u>Deviations from Qualification Tests (Chart IV)</u>

None.

#### 4.2.5 Deviations from Lot Acceptance Tests (Chart V)

None.

#### 4.3 MECHANICAL REQUIREMENTS

#### 4.3.1 <u>Dimension Check</u>

The dimensions of the transistors specified herein shall be checked. They shall conform to those shown in Figure 2.

#### 4.3.2 Weight

The maximum weight of the transistors specified herein shall be 28.5 grammes.



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#### 4.3.3 Terminal Strength

The requirements for terminal strength testing are specified in Section 9 of ESA/SCC Generic Specification No. 5000. The test conditions shall be as follows:-

#### Terminal:

Test Condition:

'A' (Tension).

Applied Force:

10 lb.

**Duration:** 

15 seconds.

#### Stud:

**Test Condition:** 

'D2' (Stud Torque).

Applied Torque:

20 lb-in.

Duration:

15 seconds.

#### 4.4 MATERIALS AND FINISHES

The materials and finishes shall be as specified herein. Where a definite material is not specified, a material which will enable the transistors specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material does not guarantee acceptance of the finished product.

#### 4.4.1 <u>Case</u>

The case shall be hermetically sealed and have a metal body with hard glass seals.

#### 4.4.2 <u>Lead Material and Finish</u>

The lead material shall be Type 'D' with either Type '2' or Type '3 or 4' finish in accordance with the requirements of ESA/SCC Basic Specification No. 23500. (See Table 1(a) for Type Variants).

#### 4.5 MARKING

#### 4.5.1 General

The marking of all components delivered to this specification shall be in accordance with the requirements of ESA/SCC Basic Specification No. 21700. Each component shall be marked in respect of:-

- (a) The SCC Component Number.
- (b) Traceability Information.

#### 4.5.2 Lead Identification

Leads shall be positioned as shown in Figure 2. No lead identification shall be marked on the part.



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#### 4.5.3 The SCC Component Number

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:-

	<u>520800502</u> <u>В</u>
Detail Specification Number	
Type Variant (see Table 1(a))	
Testing Level (B or C, as applicable)	

#### 4.5.4 Traceability Information

Each component shall be marked in respect of traceability information in accordance with the requirements of ESA/SCC Basic Specification No. 21700.

#### 4.5.5 Marking of Small Components

When it is considered that the component is too small to accommodate the marking as specified above, as much as space permits shall be marked. The order of precedence shall be as follows:-

- (a) Lead Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

The marking information in full shall accompany each component in its primary package.

#### 4.6 <u>ELECTRICAL MEASUREMENTS</u>

#### 4.6.1 <u>Electrical Measurements at Room Temperature</u>

The parameters to be measured at room temperature are scheduled in Table 2. Unless otherwise specified, measurements shall be performed at  $T_{amb}$  = +25 ±3 °C.

#### 4.6.2 Electrical Measurements at High and Low Temperatures

The parameters to be measured at high and low temperatures are scheduled in Table 3. The measurements shall be performed at  $T_{amb} = -55(+5-0)$  and +150(+0-5) °C respectively.



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#### 4.6.3 Circuits for Electrical Measurements

Circuits for use in performing the electrical measurements listed in Tables 2 and 3 are shown, where applicable, in MIL-STD-750 and in Figure 4 of this specification.

#### 4.7 BURN-IN TESTS

#### 4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, measurements shall be performed at  $T_{amb}$  = +25 ±3 °C. The parameter drift values ( $\Delta$ ) applicable to the parameters scheduled shall not be exceeded. In addition to these drift value requirements, the appropriate limit value specified for a given parameter in Table 2 shall not be exceeded.

#### 4.7.2 Conditions for Burn-in

The requirements for burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 5000. The conditions for burn-in shall be as specified in Table 5 of this specification.

#### 4.7.3 Electrical Circuits for Burn-in

Not applicable.



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#### TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS

NI-	CLIADACTEDISTICS	SYMBOL	MIL-STD-750	TECT CONDITIONS	LIN	IITS	UNIT
No.	CHARACTERISTICS	SYMBOL	TEST METHOD	TEST CONDITIONS	MIN	MAX	UNIT
1	Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	3001 Bias Cond. D	I <sub>C</sub> = 200μA I <sub>E</sub> = 0A	150	-	V
2	Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	3011 Bias Cond. D	I <sub>C</sub> = 200mA I <sub>B</sub> = 0A Note 1	120	-	V
2	Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	3026 Bias Cond. D	I <sub>E</sub> = 1.0mA I <sub>C</sub> = 0A	10	-	٧
4	Collector-Emitter Cut-off Current	I <sub>CES</sub>	3041 Bias Cond. C	V <sub>BE</sub> = 0V V <sub>CE</sub> = 120V	-	1.0	mA
5	Emitter Cut-off Current	I <sub>EBO</sub>	3061 Bias Cond. D	V <sub>EB</sub> = 8.0V I <sub>C</sub> = 0A	-	1.0	mA
6	D.C. Forward Current Transfer Ratio 1	h <sub>FE1</sub>	3076	V <sub>CE</sub> = 2.0V I <sub>C</sub> = 50A Note 1	10	40	٠
7	D.C. Forward Current Transfer Ratio 2	h <sub>FE2</sub>	3076	V <sub>CE</sub> = 2.0V I <sub>C</sub> = 30A Note 1	20	-	-
8	Collector Saturation Voltage	V <sub>CE(SAT)</sub>	3071	I <sub>C</sub> = 50A I <sub>B</sub> = 5.0A Note 1	-	0.6	٧
9	Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	3066	I <sub>C</sub> = 50A V <sub>CE</sub> = 5.0V Note 1	-	1.4	٧

#### **NOTES**

- 1. Pulsed measurement: Pulse Width ≤300μs, Duty Cycle ≤2.0%.
- 2. If more than 20 units have to be measured, the measurements shall be made on a sample basis in accordance with Para. 7.4.2 of ESA/SCC Generic Specification No. 5000. Inspection Level II with an AQL = 1.0%.



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# TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - a.c. PARAMETERS

No. CHARACTERIS	CHARACTERISTICS	S SYMBOL	MIL-STD-750	TEST	TEST CONDITIONS	LIMITS		UNIT
NO.	OHAHAOTEHIOHOO	STWIDOL	TEST METHOD	FIG.	(NOTE 2)	MIN	MAX	UNIT
10	A.C. Small Signal Current Gain	h <sub>fe</sub>	3206	-	V <sub>CE</sub> = 10V I <sub>C</sub> = 1.0A f = 100kHz	8.0	-	-
11	Turn-on Time	t <sub>on</sub>	-	4	I <sub>C</sub> = 15A I <sub>B1</sub> = I <sub>B2</sub> = 1.5A	-	6.0	μs
	Turn-off Time	t <sub>off</sub>			1B1 - 1B2 - 1.5A	~	10	

**NOTES:** See Page 16.



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#### TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES

No	No. CHARACTERISTICS	HARACTERISTICS SYMBOL MIL-STD-7	MIL-STD-750	TEST CONDITIONS	LIMITS		UNIT
INO.	CHARACTERISTICS	STINIBUL	TEST METHOD TEST CONDITIONS		MIN	MAX	UNIT
4	Collector-Emitter Cut-off Current	ICES	3041 Bias Cond. C	$T_{amb}$ = + 150°C $V_{CE}$ = 120V $V_{BE}$ = 0V Note 1	-	10	mA
6	D.C. Forward Current Transfer Ratio 1	h <sub>FE1</sub>	3076	$T_{amb} = -55$ °C $I_C = 50A$ $V_{CE} = 2.0V$ Note 1	5.0	-	-

#### **NOTES**

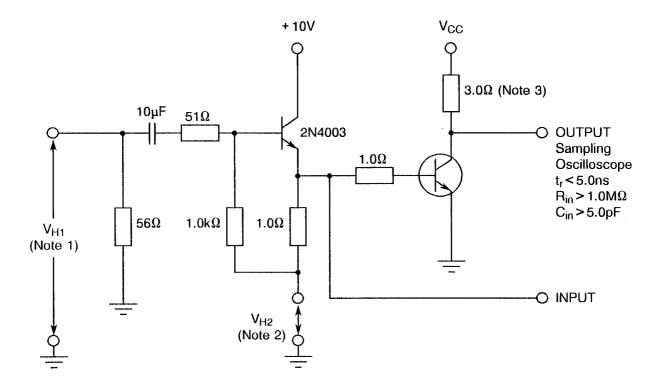
1. Pulsed measurement: Pulse Width ≤300μs, Duty Cycle ≤2.0%.

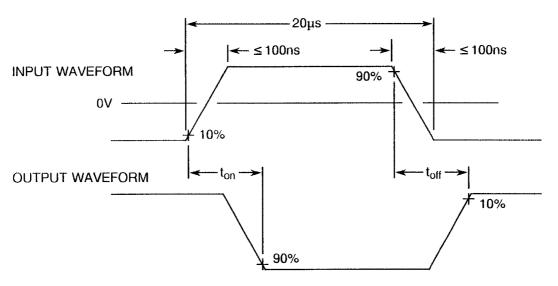
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#### FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS

#### **TURN-ON AND TURN-OFF TIME**





#### **NOTES**

- 1. Adjust  $V_{H1}$  for  $I_{B1}$ .
- 2. Adjust  $V_{H2}$  for  $I_{B2}$ .
- 3. All resistors are non-inductive.
- 4. Pulse rate ≤1.0Hz.



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#### **TABLE 4 - PARAMETER DRIFT VALUES**

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS (Δ)	UNIT
4	Collector-Emitter Cut-off Current	I <sub>CES</sub>	As per Table 2	As per Table 2	±200 or (1) +100 - 50	μ <b>A</b> %
6	D.C. Forward Current Transfer Ratio 1	h <sub>FE1</sub>	As per Table 2	As per Table 2	±20	%
8	Collector Saturation Voltage	V <sub>CE(SAT)</sub>	As per Table 2	As per Table 2	± 100	mV

#### **NOTES**

1. Whichever is greater, referred to the initial value.

#### TABLE 5 - CONDITIONS FOR POWER BURN-IN AND OPERATING LIFE TESTS

No.	CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT
1	Ambient Temperature	T <sub>amb</sub>	+ 100( + 0 - 5)	°C
2	Collector-Base Voltage	$V_{CB}$	40	٧
3	Power Dissipation	P <sub>tot</sub>	200	W
4	Test Method 1039 of MIL-STD-750	-	В	-



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# 4.8 <u>ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESA/SCC GENERIC SPECIFICATION NO. 5000)</u>

#### 4.8.1 Electrical Measurements on Completion of Environmental Tests

The parameters to be measured on completion of environmental tests are scheduled in Table 2. The measurements shall be performed at  $T_{amb} = +25 \pm 3$  °C.

#### 4.8.2 <u>Electrical Measurements at Intermediate Points during Endurance Tests</u>

The parameters to be measured at intermediate points during endurance tests are scheduled in Table 6 of this specification.

#### 4.8.3 Electrical Measurements on Completion of Endurance Tests

The parameters to be measured on completion of endurance testing are scheduled in Table 6 of this specification. The measurements shall be performed at  $T_{amb} = +25 \pm 3$  °C.

#### 4.8.4 Conditions for Operating Life Tests (Part of Endurance Testing)

The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 5000. The conditions for operating life testing shall be the same as specified in Table 5 for the burn-in test.

#### 4.8.5 Electrical Circuits for Operating Life Tests

Not applicable.

#### 4.8.6 Conditions for High Temperature Storage Test (Part of Endurance Testing)

The requirements for the high temperature storage test are specified in ESA/SCC Generic Specification No. 5000. The conditions for high temperature storage shall be  $T_{amb}$  = +200(+0-5) °C.



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# TABLE 6 - ELECTRICAL MEASUREMENTS INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTING

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	LIMITS		UNIT
					MIN.	MAX.	ONIT
4	Collector-Emitter Cut-off Current	I <sub>CES</sub>	As per Table 2	As per Table 2	-	1.0	mA
6	D.C. Forward Current Transfer Ratio 1	h <sub>FE1</sub>	As per Table 2	As per Table 2	10	40	-